

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comment s	Error Definition	Error ro rs
1	BRS	L1	10601	TFT or (thin near2 film near2 transistor\$1)	USPA T	2001/09/2 0 16:59			0
				((gate near3 insulat\$4) or (gate near3 dielectric) same (silicon near2 nitride or SiN) and (silicon near2 oxide or SiO)					
2	BRS	L2	2963		USPA T	2001/09/2 0 17:00			0
3	BRS	L3	356	Hydrogen and 1 and 2	USPA T	2001/09/2 0 16:59			0
				TFT or (thin near2 film near2 transistor\$1)	US-P GPUB	2001/09/2 0 17:00			
4	BRS	L4	478						0
5	BRS	L5	155	((gate near3 insulat\$4) or (gate near3 dielectric) same (silicon near2 nitride or SiN) and (silicon near2 oxide or SiO)	US-P GPUB	2001/09/2 0 16:59			0
6	BRS	L6	36	Hydrogen and 4 and 5	US-P GPUB	2001/09/2 0 17:00			0
				TFT or (thin near2 film near2 transistor\$1)	EPO	2001/09/2 0 17:01			
7	BRS	L7	1984						0
8	BRS	L8	57	((gate near3 insulat\$4) or (gate near3 dielectric) same (silicon near2 nitride or SiN) and (silicon near2 oxide or SiO)	EPO	2001/09/2 0 17:01			0

Type	L #	Hits	Search Text	DBS	Time Stamp	Comments	Error Definition	Errors
9	BRS	L9	0	Hydrogen and 7 and 8	EPO	2001/09/2 0 17:02		0
10	BRS	L10	11495 film near2 transistor\$1)	TFT or (thin near2 JPO	2001/09/2 0 17:02			0
			((gate near3 insula\$4) or (gate near3 dielectric) same (silicon near2 nitride or SiN) and (silicon near2 oxide or SiO)	JPO				
11	BRS	L11	526	Hydrogen and 10 and 11	JPO	2001/09/2 0 17:02		0
12	BRS	L12	12	TFT or (thin near2 transistor\$1)	JPO	2001/09/2 0 17:03		0
13	BRS	L13	13363	((gate near3 insula\$4) or (gate near3 dielectric) same (silicon near2 nitride or SiN) and (silicon near2 oxide or SiO)	DERW ENT	2001/09/2 0 17:02		0
14	BRS	L14	262	Hydrogen and 13 and 14	DERW ENT	2001/09/2 0 17:03		0
15	BRS	L15	3	Hydrogen and 13 and 14	DERW ENT	2001/09/2 0 17:03		0